GaAs SPDT Svitch
DC-2. GHz

## Features

- Very Low Power Consumption: $100 \mu \mathrm{~W}$
- Low Insertion Loss: 0.5 dB
- High Isolation: 25 dB up to 2 GHz
- Very High Intercept Point: 45 dBm IP3
- Nanosecond Switching Speed
- Temperature Range: $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$
- Low Cost SOIC-8 Plastic Package
- Tape and Reel Packaging Available


## Description

M/A-COM's SW-239 is a GaAs MMIC SPDT switch in a low cost SOIC-8 lead surface mount plastic package. The SW-239 is ideally suited for use where low power consumption is required.

Typical applications include transmit/receive switching, switch matrices and switched filter banks in systems such as radio and cellular equipment, PCM, GPS, fiber optic modules, and other battery powered radio equipment.

The SW-239 is fabricated using a monolithic GaAs MMIC using a mature 1 micron process. The process features full chip passivation for increased performance and reliability.

## Ordering Information ${ }^{1}$

| Part Number | Package |
| :---: | :---: |
| SW-239 | Bulk Packaging |
| SW-239TR | 1000 piece reel |

1. Reference Application Note M513 for reel size information.

## Functional Schematic



## Pin Configuration

| Pin No. | Function | Pin No. | Function |
| :---: | :---: | :---: | :---: |
| 1 | RF Common | 5 | Control B |
| 2 | Ground | 6 | RF Port 2 |
| 3 | RF Port 1 | 7 | Ground |
| 4 | Control A | 8 | Ground |

Absolute Maximum Ratings ${ }^{2,3}$

| Parameter | Absolute Maximum |
| :---: | :---: |
| Input Power |  |
| 0.05 GHz |  |
| $0.5-2.0 \mathrm{GHz}$ | +27 dBm |
| Control Voltage | +34 dBm |
| Operating Temperature | $-8.5 \mathrm{~V} \leq \mathrm{V}_{\mathrm{C}} \leq+5 \mathrm{~V}$ |
| Storage Temperature | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |
| St | $-65^{\circ} \mathrm{C}$ to $+150^{\circ} \mathrm{C}$ |

2. Exceeding any one or combination of these limits may cause
permanent damage to this device.
3/A-COM does not recommend sustained operation near
these survivability limits.

## GaAs SPDT Svitch DC-25GHz

Electrical Specifications: $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}, \mathrm{V}_{\mathrm{C}}=0 \mathrm{~V} /-5 \mathrm{~V}, \mathrm{Z}_{0}=50 \mathrm{Ohms}^{4}$

| Parameter | Test Conditions | Units | Min | Typ | Max |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Insertion Loss | $\begin{aligned} & \mathrm{DC}-0.1 \mathrm{GHz} \\ & \mathrm{DC}-0.5 \mathrm{GHz} \\ & \mathrm{DC}-1.0 \mathrm{GHz} \\ & \mathrm{DC}-2.0 \mathrm{GHz} \end{aligned}$ | dB <br> dB <br> dB <br> dB | - - - | $\begin{aligned} & 0.4 \\ & 0.4 \\ & 0.5 \\ & 0.6 \end{aligned}$ | $\begin{aligned} & - \\ & 0.8 \\ & - \end{aligned}$ |
| Isolation | $\begin{aligned} & \mathrm{DC}-0.1 \mathrm{GHz} \\ & \mathrm{DC}-0.5 \mathrm{GHz} \\ & \mathrm{DC}-1.0 \mathrm{GHz} \\ & \mathrm{DC}-2.0 \mathrm{GHz} \end{aligned}$ | dB <br> dB <br> dB <br> dB | $\begin{aligned} & - \\ & \overline{30} \end{aligned}$ | $\begin{aligned} & 56 \\ & 43 \\ & 33 \\ & 24 \end{aligned}$ | — — |
| VSWR | DC - 2.0 GHz | Ratio | - | 1.2:1 | - |
| Trise, Tfall | 10\% to $90 \% \mathrm{RF}, 90 \%$ to $10 \% \mathrm{RF}$ | nS | - | 2 | - |
| Ton, Toff | 50\% Control to 90\% RF, 50\% Control to 10\% RF | nS | - | 4 | - |
| Transients | In-Band | mV | - | 15 | - |
| 1 dB Compression Point | Input Power, 0.05 GHz Input Power, $0.5-2.0 \mathrm{GHz}$ | dBm dBm | - | $\begin{aligned} & 21 \\ & 27 \end{aligned}$ | - |
| 2nd Order Intercept | Measured Relative to Input Power (for two-tone input power up to +6 dBm ) $\begin{gathered} 0.05 \mathrm{GHz} \\ 0.5-2.0 \mathrm{GHz} \end{gathered}$ | dBm dBm | - | $\begin{aligned} & 55 \\ & 68 \end{aligned}$ | - |
| 3rd Order Intercept | Measured Relative to Input Power (for two-tone input power up to +6 dBm ) $\begin{gathered} 0.05 \mathrm{GHz} \\ 0.5-2.0 \mathrm{GHz} \end{gathered}$ | dBm dBm | - | $\begin{aligned} & 40 \\ & 45 \end{aligned}$ | - |
| Control Current | $\left\|\mathrm{V}_{\mathrm{C}}\right\|=5 \mathrm{~V}$ | $\mu \mathrm{A}$ | - | 20 | 25 |

4. For positive voltage control, external DC blocking capacitors are required on all RF ports.

## SOIC-8



ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.
PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

- North America Tel: 800.366.2266 / Fax: 978.366.2266
- Europe Tel: 44.1908.574.200 / Fax: 44.1908.574.300
- Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298

Visit www.macomtech.com for additional data sheets and product information.

## Electrical Schematic



## Typical Performance Curves

## Insertion Loss



VSWR


3

ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.
PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology
Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

## Truth Table ${ }^{5}$

| Control Inputs |  | Condition of Switch <br> RF Common to Each RF <br> Port |  |
| :---: | :---: | :---: | :---: |
| A | B | RF1 | RF2 |
| 1 | 0 | On | Off |
| 0 | 1 | Off | On |

5. $0=0 \mathrm{~V}$ to $-0.2 \mathrm{~V}, 1=-5 \mathrm{~V}$ to -8 V

## Isolation


$\qquad$

